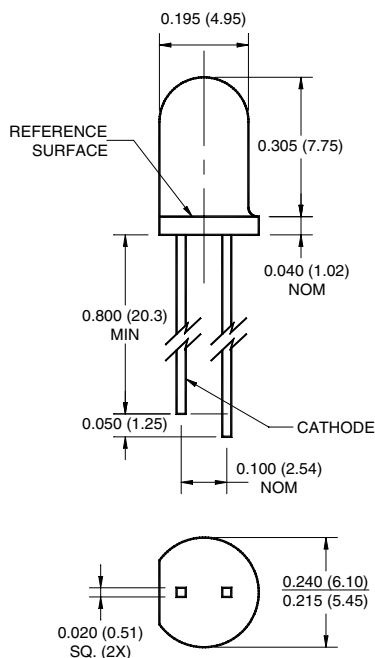


QED233

QED234

PACKAGE DIMENSIONS

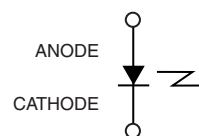


NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The QED233 / QED234 is a 940 nm GaAs / AlGaAs LED encapsulated in a clear untinted, plastic T-1 3/4 package.

FEATURES

- $\lambda = 940$ nm
- Chip material = GaAs with AlGaAs window
- Package type: T-1 3/4 (5mm lens diameter)
- Matched Photosensor: QSD122/123/124
- Medium Emission Angle, 40°
- High Output Power
- Package material and color: Clear, untinted, plastic
- Ideal for remote control applications

QED233

QED234

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	T _{OPR}	-40 to +100	°C
Storage Temperature	T _{STG}	-40 to +100	°C
Soldering Temperature (Iron) ^(2,3,4)	T _{SOL-I}	240 for 5 sec	°C
Soldering Temperature (Flow) ^(2,3)	T _{SOL-F}	260 for 10 sec	°C
Continuous Forward Current	I _F	100	mA
Reverse Voltage	V _R	5	V
Power Dissipation ⁽¹⁾	P _D	200	mW
Peak Forward Current	I _{FP}	1.5	A

1. Derate power dissipation linearly 2.67 mW/°C above 25°C.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6mm) minimum from housing.
5. Pulse conditions; tp = 100 μs, T = 10 ms.

ELECTRICAL / OPTICAL CHARACTERISTICS (T_A = 25°C)

PARAMETER	TEST CONDITIONS	DEVICE	SYMBOL	MIN	TYP	MAX	UNITS
Peak Emission Wavelength	I _F = 20 mA	ALL	λ _{PE}	—	940	—	nm
Spectral Bandwidth	I _F = 20 mA	ALL	—	50	—	nm	
Temp. Coefficient of λ _{PE}	I _F = 100 mA	ALL	TC _λ	—	0.2	—	nm/K
Emission Angle	I _F = 100 mA	ALL	2θ _{1/2}	—	40	—	Deg.
Forward Voltage	I _F = 100 mA, tp = 20 ms	ALL	V _F	—	—	1.6	V
Temp. Coefficient of V _F	I _F = 100 mA	ALL	TC _V	—	-1.5	—	mV/K
Reverse Current	V _R = 5 V	ALL	I _R	—	—	10	μA
Radiant Intensity	I _F = 100 mA, tp = 20 ms	QED233	I _E	10	—	50	mW/sr
		QED234		27	—	—	
Temp. Coefficient of I _E	I _F = 20 mA	ALL	TC _I	—	-0.6	—	%/K
Rise Time	I _F = 100 mA	ALL	t _r	—	1000	—	ns
Fall Time		ALL	t _f	—	1000	—	

QED233

QED234

TYPICAL PERFORMANCE CURVES TBD

Fig. 1 Normalized Radiant Intensity vs. Forward Current

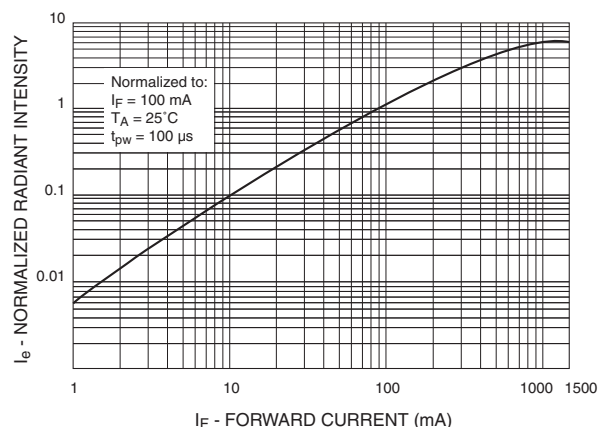


Fig. 2 Forward Voltage Vs. Ambient Temperature

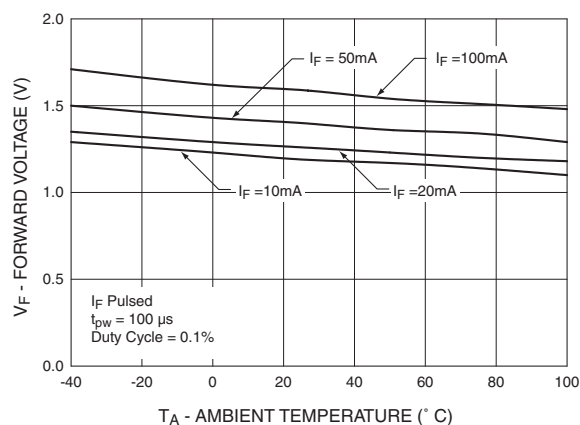


Fig. 3 Normalized Radiant Intensity vs. Wavelength

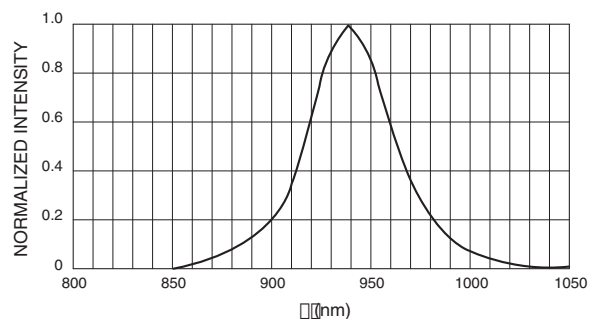


Fig. 4 Radiation Diagram

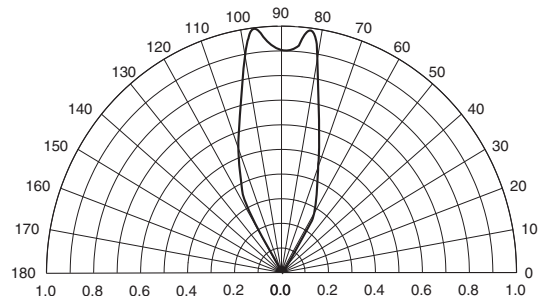
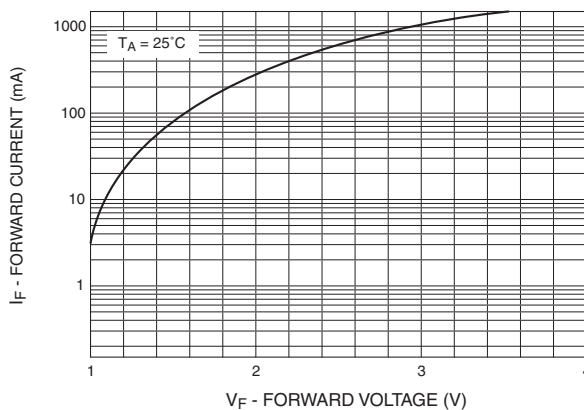


Fig. 5 Forward Current vs. Forward Voltage



QED233

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